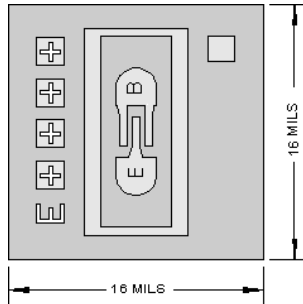


**Chip Type 2C3960**  
**Geometry 0003**  
**Polarity NPN**

**Generic Packaged Part:**  
**2N3960**



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Chip type **2C3960** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

2N3960, 2N3960UB, SD3960F, SQ3960, SQ3960F

**Product Summary:**

**APPLICATIONS:**

Designed for high-speed current-mode logic switching.

**Features:**

Mechanical Specifications		
Metallization	Top	Al - 15 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	2.7 mils x 2.7 mils
	Base	2.7 mils x 2.7 mils
Die Thickness	8 mils nominal	
Chip Area	16 mils x 16 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
T <sub>A</sub> = 25°C				
Parameter	Test conditions	Min	Max	Unit
BV <sub>CEO</sub>	I <sub>C</sub> = 10.0 mA	12	---	V dc
BV <sub>CBO</sub>	I <sub>C</sub> = 10 µA	20	---	V dc
BV <sub>EBO</sub>	I <sub>E</sub> = 10.0 mA	4.5	---	V dc
I <sub>CEX</sub>	V <sub>CE</sub> = 10 V, V <sub>EB</sub> = 2.0 V	---	5.0	nA
h <sub>FE1</sub>	I <sub>C</sub> = 1.0 mA dc, V <sub>CE</sub> = 1.0 V	25	---	---
h <sub>FE2</sub>	I <sub>C</sub> = 10 mA dc, V <sub>CE</sub> = 1.0 V	40	400	---
h <sub>FE3</sub>	I <sub>C</sub> = 30 mA dc, V <sub>CE</sub> = 1.0 V	25	---	---
V <sub>CE(sat)</sub>	I <sub>C</sub> = 30 mA dc, I <sub>B</sub> = 3.0 mA	---	0.3	V dc

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 µs, duty cycle less than 2%.*